January 2000

ADVANCE INFORMATION



FDD3670 100V N-Channel PowerTrench[®] MOSFET

General Description

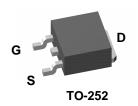
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

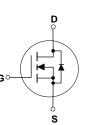
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\text{DS(ON)}}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 34 A, 100 V. $R_{DS(ON)} = 0.030 \ \Omega \ @ V_{GS} = 10 \ V$ $R_{DS(ON)} = 0.033 \ \Omega \ @ V_{GS} = 6 \ V$
- Low gate charge (57 nC typical)
- Fast switching speed
- High performance trench technology for extremely low R_{DS(ON)}
- High power and current handling capability.





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	V
ID	Drain Current – Continuous	(Note 1)	34	A
	Drain Current – Pulsed		100	
PD	Maximum Power Dissipation @ $T_c = 25^{\circ}C$	(Note 1)	70	W
	@ T _A = 25°C	(Note 1a)	3.2	
	@ T _A = 25°C	(Note 1b)	1.3	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics R_{0JC} Thermal Resistance, Junction-to-Case (Note 1) 1.8 °C/W R_{0JA} Thermal Resistance, Junction-to-Ambient (Note 1b) 96 °C/W

Package Marking and Ordering Information

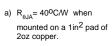
Device Marking	Device	Reel Size	Tape width	Quantity
FDD3670	FDD3670	13"	16mm	2500 units
	•	•	•	

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FDD3670

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	100			V
<u>ΔBV_{DSS}</u> ΔTj	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, Referenced to 25°C		92		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			25	μA
I _{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V} \qquad V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)	-	•	•		
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	2	2.5	4	V
$\Delta V_{GS(th)} \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, Referenced to 25°C		-7.2		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$ \begin{array}{ccc} V_{GS} = 10 \ V, & I_D = 7.3 \ A \\ V_{GS} = 10 \ V, & I_D = 7.3 \ A \\ T_J = 125^\circ C \\ V_{J} = 0 \ A \end{array} $		0.022 0.039 0.024	0.030 0.060 0.033	Ω
	On-State Drain Current	$V_{GS} = 6 V,$ $I_D = 7.0 A$ $V_{GS} = 10 V,$ $V_{DS} = 5 V$	25	0.024	0.033	А
l _{D(on)} g _{FS}	Forward Transconductance	$V_{\rm GS} = 10$ V, $V_{\rm DS} = 3$ V $V_{\rm DS} = 5$ V, $I_{\rm D} = 7.3$ A	23	31		s
-				01		
Dynamic C _{iss}	Characteristics	$V_{DS} = 50 V$, $V_{GS} = 0 V$,		2490		pF
	Output Capacitance	f = 1.0 MHz		265		pF
C _{rss}	Reverse Transfer Capacitance			80		pF
	·					
	IG Characteristics (Note 2) Turn–On Delay Time	$V_{DD} = 50 V$, $I_D = 1 A$,		16	26	ns
t _r	Turn–On Rise Time	$V_{\text{GS}} = 10 \text{ V}, \qquad \text{R}_{\text{GEN}} = 6 \Omega$		10	18	ns
t _{d(off)}	Turn–Off Delay Time			56	84	ns
t _f	Turn–Off Fall Time	-		25	40	ns
Q _g	Total Gate Charge	$V_{DS} = 50 V$, $I_D = 25 A$,		57	80	nC
Q _{gs}	Gate–Source Charge	$V_{GS} = 10 V$		11		nC
Q _{gd}	Gate-Drain Charge	-		15		nC
Drain-Se	ource Diode Characteristics	and Maximum Ratings	•	•		
l _s	Maximum Continuous Drain–Source				2.7	А
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V$, $I_S = 2.7 A$ (Note 2)			1.2	V



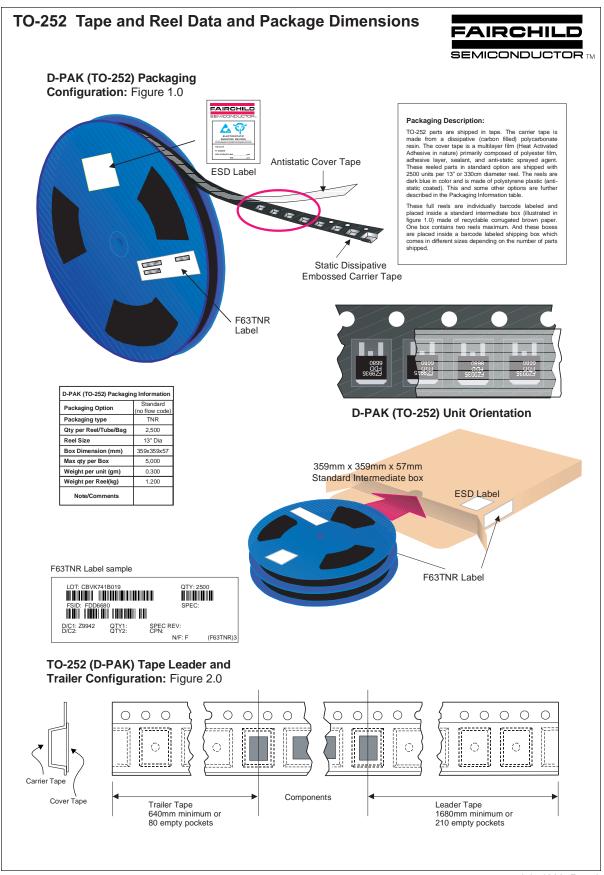




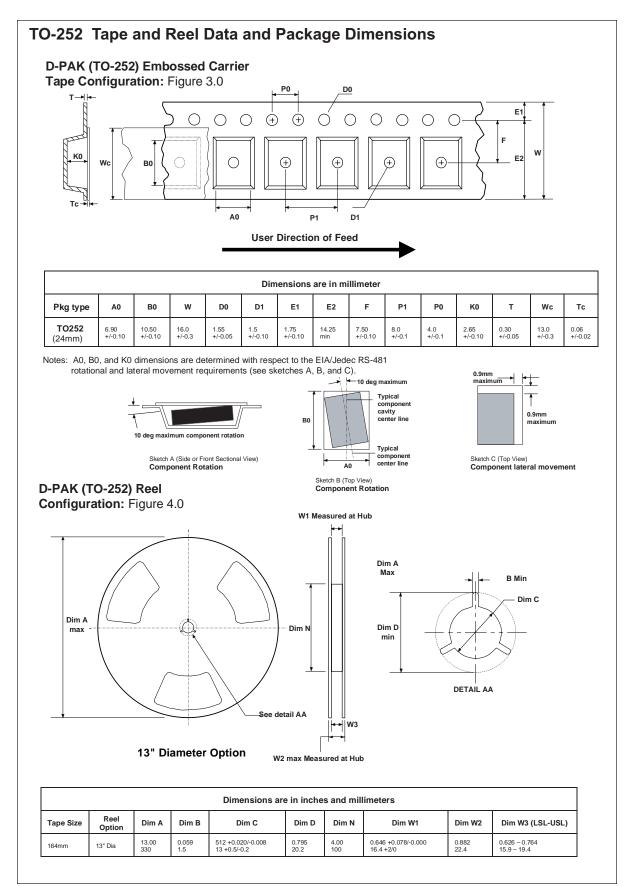
b) $R_{\theta JA}$ = 96^oC/W on a minimum mounting pad.

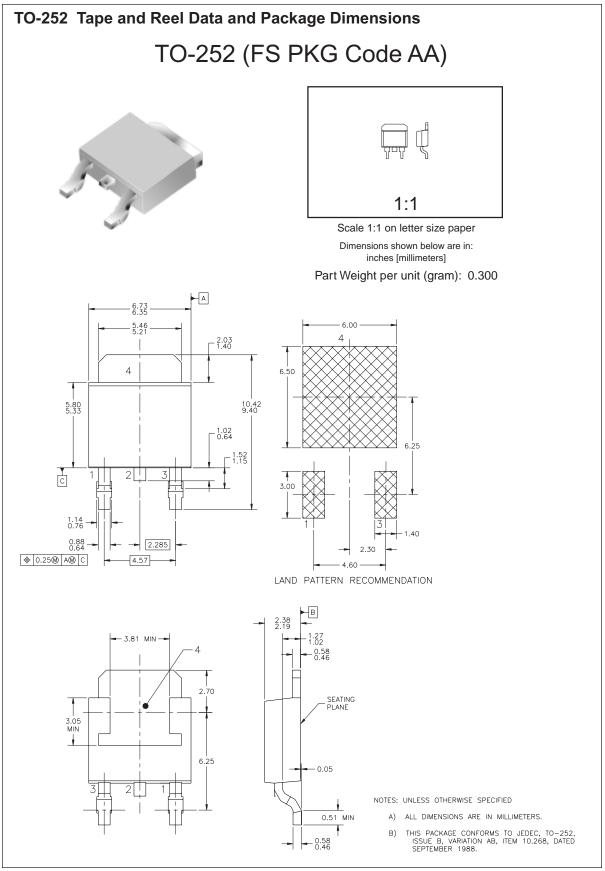
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%



July 1999, Rev. A





September 1999, Rev. A

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Datasheet Identification	Product Status	Definition
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